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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10045895	10/29/2001	438		2823	

**APPLICANTS: Park Stenhen.

**CONTINUING DATA VERIFIED: *See*
THIS APPLICATION IS A CON OF 09/493,384 01/28/2000 PAT 6,355,555

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STATEMENT OF CLAIMS:
The term of this patent shall not extend
beyond the expiration date
of Pat. No. *6,355,555*

** FOREIGN APPLICATIONS VERIFIED: *See*
NONE

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	ATTORNEY DOCKET NO
Foreign priority claimed 35 USC 119 conditions met Verified and Acknowledged Examiners initials		<input type="checkbox"/> yes <input checked="" type="checkbox"/> no <input type="checkbox"/> yes <input checked="" type="checkbox"/> no	2000.029996/TT3586C
TITLE : Method of fabricating copper-based semiconductor devices using a sacrificial dielectric layer <small>RECEIVED ON COMM-PAT 3 14 2002 BY RAY J. H.</small>			

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING		
Amount Due	Date Paid	Sheets Drwg.		Fig.s Drwg.
				Print Fig.
TERMINAL		Primary Examiner		
DISCLAIMER		PREPARED FOR ISSUE		Application Examiner
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